

1N914

SWITCHING DIODES

VOLTAGE 100 Volt **POWER** 500 mWatt

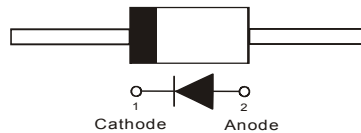
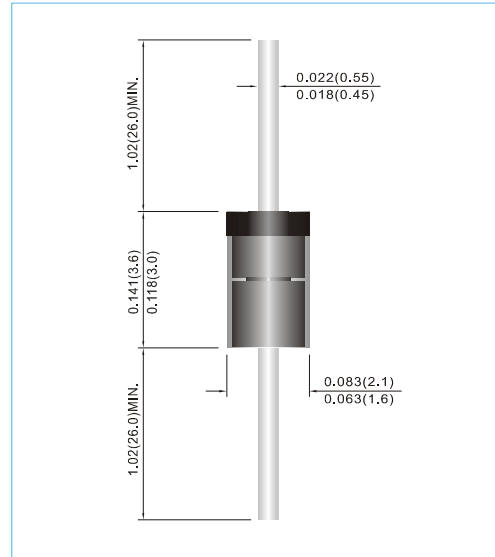
DO-35 Unit : inch(mm)

FEATURES

- Fast switching Speed.
- Electrically Identical to Standard JEDEC
- High Conductance
- Axial lead Package Ideally Suited for Automatic Insertion.
- Lead free in compliance with EU RoHS 2011/65/EU directive

MECHANICAL DATA

- Case: Molded Glass DO-35
- Terminals: Solderable per MIL-STD-750, Method 2026
- Packing information
 - B/P - 2K per Bulk box
 - T/R - 10K per 15" Reel
 - T/B - 5K per horiz. tape & Ammo box



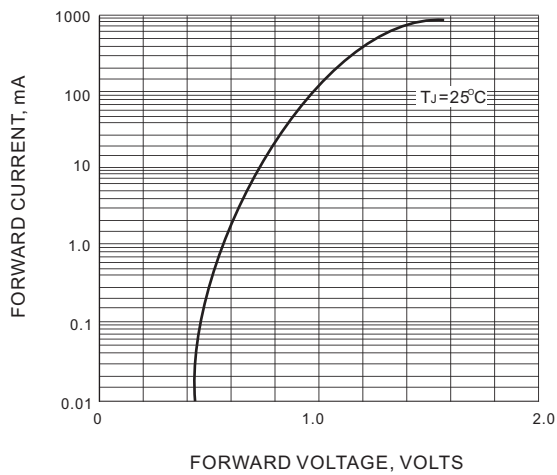
MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

PARAMETER	SYMBOL	1N914	UNITS
Reverse Voltage	V _R	75	V
Peak Reverse Voltage	V _{RM}	100	V
RMS Voltage	V _{RMS}	50	V
Maximum Average Forward Current at T _A =25°C And f ≥ 50Hz	I _{F(AV)}	75	mA
Surge Forward Current at t < 1s and T _J =25 °C	I _{FSM}	500	mA
Power Dissipation at Tamb= 25 °C	P _{TOT}	500	mW
Maximum Forward Voltage at I _F =10mA	V _F	1.0	V
Maximum Leakage Current at V _R =20V at V _R =75V at V _R =20V, T _J = 150 °C	I _R	25 5 50	nA μA μA
Maximum Capacitance (Note 1)	C _J	4	pF
Maximum Reverse Recovery Time (Note 2)	t _{rr}	4	ns
Typical Thermal Resistance	R _{θJA}	350	°C / W
Junction Temperature and Storage Temperature Range	T _J , T _S	-65 to +175	°C

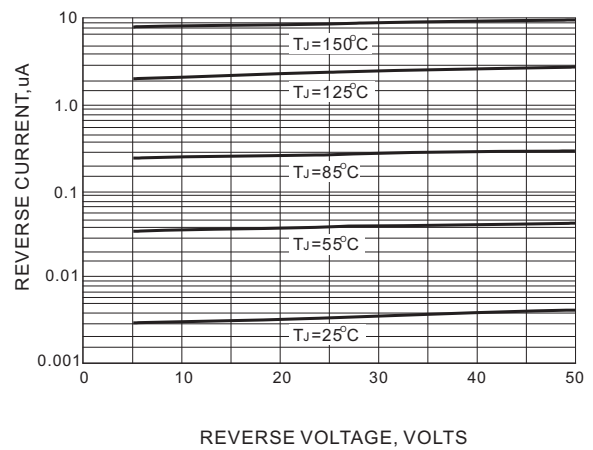
NOTE:

1. C_J at V_R=0, f=1MHZ
2. From I_F=10mA to I_R=1mA, V_R=6Volts, R_L=100Ω

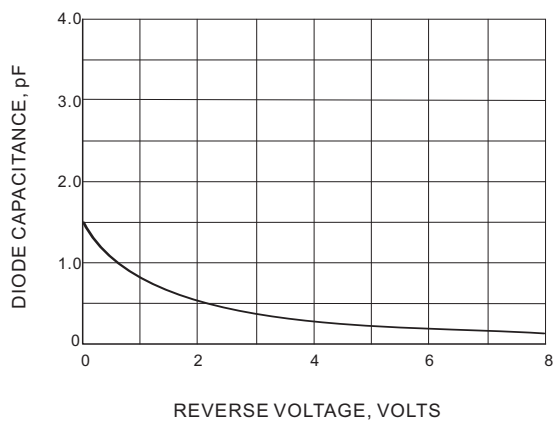
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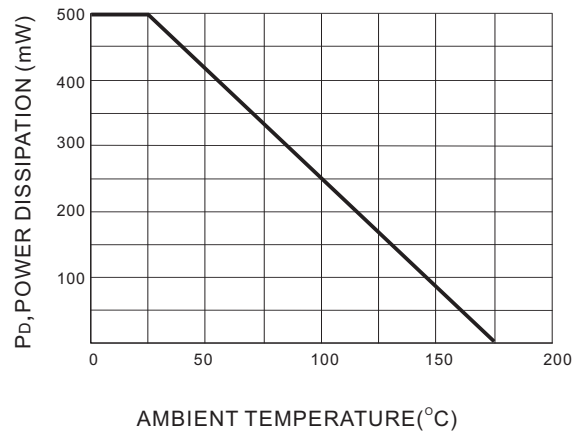
FORWARD VOLTAGE



LEAKAGE CURRENT



TYPICAL CAPATICANCE



POWER DERATING

1N914

Part No_packing code_Version

1N914_AX_10001
 1N914_AY_10001
 1N914_R2_10001
 1N914_BO_10001

For example :

RB500V-40_R2_00001



Packing Code XX				Version Code XXXXX		
Packing type	1 st Code	Packing size code	2 nd Code	HF or RoHS	1 st Code	2 nd ~5 th Code
Tape and Ammunition Box (T/B)	A	N/A	0	HF	0	serial number
Tape and Reel (T/R)	R	7"	1	RoHS	1	serial number
Bulk Packing (B/P)	B	13"	2			
Tube Packing (T/P)	T	26mm	X			
Tape and Reel (Right Oriented) (TRR)	S	52mm	Y			
Tape and Reel (Left Oriented) (TRL)	L	PANASERT T/B CATHODE UP (PBCU)	U			
FORMING	F	PANASERT T/B CATHODE DOWN (PBCD)	D			

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